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10/558367

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of

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Application Number	Not Yet Assigned
Confirmation Number	Not Yet Assigned
Filing Date	November 29, 2005
First Named Inventor	Munehiro TADA
Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	Q91732

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
		US 2003/0001282	A1	01-02-2003	Herman Meynen
		US			
		US			
		US			
		US			
		US			
		US			
		US			

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
		JP	2000-183166	A	06-30-2000	NEC CORP.	
		WO	2001/054190	A1	07-26-2001	ADVANCED MICRO DEVICES	
		WO	2002/058134	A1	07-25-2002	STMICROELECTRONICS S.A.	
		JP	2002-83870	A	03-22-2002	TOKYO ELECTRON LTD.	
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		JP	2004-200203	A	07-15-2004	SEMICONDUCTOR LEADING, et al.	
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		JP	2003-347403	A	12-05-2003	FUJITSU LTD.	

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
		Tada, M., et al. "BARRIER-METAL-FREE (BMF), Cu DUAL-DAMASCENE INTERCONNECTS WITH Cu-epi-CONTACTS BURIED IN ANTI-DIFFUSIVE, LOW-k ORGANIC FILM," 2001 Symposium on VLSI Technology, June 12, 2001, pages 13-14.	
		Tada, M., et al. "A 65nm-NODE Cu INTERCONNECT TECHNOLOGY USING POROUS SiOCH FILM (K=2.5) COVERED WITH ULTRA-THIN, LOW-k PORE SEAL (k=2.7), International Electron Devices Meeting 2003 Technical Digest, December 8-10, 2003, pages 35.2.1 to 35.2.4.	

Examiner Signature

Date Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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